



Description

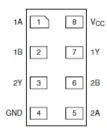
The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP2G02 is a dual two-input NOR gate. Both gates have push-pull outputs designed for operation over a power supply range of 0.8 V to 3.6 V. The device is fully specified for partial power down applications using $I_{\rm OFF}$. The $I_{\rm OFF}$ circuitry disables the output preventing damaging current backflow when the device is powered down. Each gate performs the positive Boolean function:

$$Y = \overline{A + B}$$
 or $Y = \overline{A} \bullet \overline{B}$

Pin Assignments

(Top View)



X2-DFN1210-8

Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption

 $I_{CC} < 0.9 \mu A$

• Low Dynamic Power Consumption

C_{PD} = 6 pF (Typical at 3.6V)

- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250 mV at V_{CC} = 3.0V
- I_{OFF} Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22

2000-V Human Body Model (A114)

Exceeds 1000-V Charged Device Model (C101)

- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages Named per JESD30E
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

- · Suited for Battery and Low Power Needs
- Wide array of products such as:
 - Tablets, E-readers
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders
 - PCs, Ultrabooks, Notebooks, Netbooks
 - Computer Peripherals, Hard Drives, SSD, CD/DVD ROM
 - TV, DVD, DVR, Set-Top Box

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

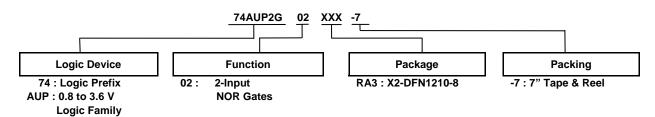
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Ordering Information

2G : Dual Gate



	Package Package Packa		Package	7" Tape and Reel		
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix	
74AUP2G02RA3-7	RA3	X2-DFN1210-8	1.2mm X 1.0mm X 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7	

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Pin Descriptions

Pin Name	Pin No.	Function
1A	1	Data Input
1B	2	Data Input
2Y	3	Data Output
GND	4	Ground
2A	5	Data Input
2B	6	Data Input
1Y	7	Data Output
V _{CC}	8	Supply Voltage

Logic Diagram

Function Table

Inp	uts	Output
Α	В	Y
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

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Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	50	mA
lok	Output Clamp Current (V _O < 0)	50	mA
Io	Continuous Output Current (V _O = 0 to V _{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes:

Recommended Operating Conditions (Note 8)

Symbol	Pa	arameter	Min	Max	Unit
Vcc	Operating Voltage	_	0.8	3.6	V
Vı	Input Voltage	1	0	3.6	V
Vo	Output Voltage		0	V _{CC}	V
		V _{CC} = 0.8V	_	-20	μA
		V _{CC} = 1.1V	_	-1.1	
	I _{OH} High-Level Output Current	V _{CC} = 1.4V	_	-1.7	
Іон		V _{CC} = 1.65V	_	-1.9	mA
		V _{CC} = 2.3V	_	-3.1	
		V _{CC} = 3.0V	_	-4	
		V _{CC} = 0.8V	_	20	μA
		V _{CC} = 1.1V	_	1.1	
		V _{CC} = 1.4V	_	1.7	
loL	Low-Level Output Current	V _{CC} = 1.65V	_	1.9	mA
	I _{OL} Low-Level Output Current	V _{CC} = 2.3V	_	3.1	
		V _{CC} = 3.0V	_	4	
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 0.8V to 3.6V	_	200	ns/V
T _A	Operating Free-Air Temperature	_	-40	+125	°C

8. Unused inputs should be held at V_{CC} or Ground. Note:

^{6.} Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device

operation should be within recommend values.

7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



Electrical Characteristics

Symbol	Parameter	Test Conditions	V	T _A = -	+25°C	T _A = -40°0	C to +85°C	Unit
Symbol	Parameter	rest Conditions	V _{CC}	Min	Max	Min	Max	Unit
		_	0.8V to 1.65V	0.80 X V _{CC}	_	0.80 X V _{CC}	_	
V _{IH}	High-Level Input	_	1.65V to 1.95V	0.65 X V _{CC}	_	0.65 X V _{CC}	_	V
VIH	Voltage	-	2.3V to 2.7V	1.6	_	1.6	_	v
			3.0V to 3.6V	2.0	_	2.0	_	
		1	0.8V to 1.65V	_	0.30 X V _{CC}	_	0.30 X V _{CC}	
V _{IL}	Low-Level Input	1	1.65V to 1.95V	_	0.35 X V _{CC}	_	0.35 X V _{CC}	V
V IL	Voltage	1	2.3V to 2.7V	_	0.7	_	0.7]
			3.0V to 3.6V		0.9		0.9	
		I _{OH} = -20μA	0.8V to 3.6V	V _{CC} – 0.1	_	V _{CC} – 0.1	_	
		$I_{OH} = -1.1 \text{mA}$	1.1V	0.75 X V _{CC}	_	0.7 X V _{CC}	_	
		$I_{OH} = -1.7 \text{mA}$	1.4V	1.11	_	1.03	_	
.,	High-Level Output	vel Output I _{OH} = -1.9mA		1.32	_	1.3	_	V
VoH	Voltage	I _{OH} = -2.3mA	2.21/	2.05	_	1.97	_	V
		I _{OH} = -3.1mA	2.3V	1.9	_	1.85	_	
	l F	I _{OH} = -2.7mA	- 3V	2.72	_	2.67	_	
		I _{OH} = -4mA	30	2.6	_	2.55	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.1	_	0.1	
		I _{OL} = 1.1mA	1.1V	_	0.3 X V _{CC}	_	0.3 X V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.31	_	0.37	
.,	Low-Level Input	I _{OL} = 1.9mA	1.65V	_	0.31	_	0.35	.,
Vol	Voltage	I _{OL} = 2.3mA	0.01/	_	0.31	_	0.33	V
		I _{OL} = 3.1mA	2.3V	_	0.44	_	0.45	
		I _{OL} = 2.7mA	0) /	_	0.31	_	0.33	
		I _{OL} = 4mA	3V	_	0.44	_	0.45	
II	Input Current	A or B Input V _I = GND to 3.6V	0V to 3.6V	_	± 0.1	_	± 0.5	μΑ
I _{OFF}	Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0V	_	± 0.2	_	± 0.6	μΑ
Δl _{OFF}	Delta Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	± 0.2	_	± 0.6	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	0.5	_	0.9	μA
ΔI _{CC}	Additional Supply Current	One Input at V _{CC} –0.6V Other Inputs at V _{CC} or GND	3.3V	_	40	_	50	μA



Electrical Characteristics (continued)

Symbol	Parameter	Test Conditions	V	T _A = -40°C	to +125°C	Unit	
Syllibol	Faranietei	rest conditions	V _{CC}	Min	Max	Onit	
		_	0.8V to 1.65V	0.80 X V _{CC}	_		
V_{IH}	High-Level Input Voltage	_	1.65V to 1.95V	0.70 X V _{CC}	_	V	
VIH	Trigit-Level input voltage	_	2.3V to 2.7V	1.6	_	V	
		_	3.0V to 3.6V	2.0	_		
		_	0.8V to 1.65V	_	0.25 X V _{CC}		
V_{IL}	Low-Level Input Voltage	_	1.65V to 1.95V	1	0.30 X V _{CC}	V	
V IL	Low Level input voltage	_	2.3V to 2.7V	_	0.7	v	
		_	3.0V to 3.6V	_	0.9		
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V _{CC} – 0.11	_		
		$I_{OH} = -1.1$ mA	1.1V	0.6 X V _{CC}	_		
		$I_{OH} = -1.7 \text{mA}$	1.4V	0.93	_		
.,	OH High-Level Output Voltage	I _{OH} = -1.9mA	1.65V	1.17		V	
VoH	High-Level Output Voltage	I _{OH} = -2.3mA	2.3V	1.77	_	V	
		I _{OH} = -3.1mA	2.3V	1.67	_		
		I _{OH} = -2.7mA	3V	2.40	_		
		I _{OH} = -4mA	30	2.30	_		
		I _{OL} = 20μA	0.8V to 3.6V	_	0.11		
		I _{OL} = 1.1mA	1.1V	_	0.33 X V _{CC}		
		I _{OL} = 1.7mA	1.4V	_	0.41		
.,	Lave Lave Hannet Vallage	I _{OL} = 1.9mA	1.65V	_	0.39		
V_{OL}	Low-Level Input Voltage	I _{OL} = 2.3mA	0.01/	_	0.36	V	
		I _{OL} = 3.1mA	2.3V	_	0.50		
		I _{OL} = 2.7mA	0) (_	0.36		
		I _{OL} = 4mA	3V	_	0.50		
l _l	Input Current	A or B Input, V _I = GND to 3.6V	0V to 3.6V	_	± 0.75	μA	
l _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V	_	± 1.0	μA	
ΔI_{OFF}	Delta Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μA	
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	3.0	μA	
Δlcc	Additional Supply Current	Input at V _{CC} –0.6V Other Inputs at V _{CC} or GND	3.3V	_	75	μΑ	

Operating and Package Characteristics (@T_A = +25°C, unless otherwise specified.)

	Parameter	Tes Condi		V _{CC}	Тур	Unit
				0.8V	5.1	
				1.2V ± 0.1V	5.2	
	Power Dissipation	f = 1N	ИHz	1.5V ± 0.1V	5.2]
C_{pd}	Capacitance	No Lo	oad	1.8V ± 0.15V	5.5	pF
				2.5V ± 0.2V	5.7	1
				3.3V ± 0.3V	6.0	
C _i	Input Capacitance	$V_i = V_{CC}$	or GND	0V or 3.3V	2.0	pF
θ _{JA}	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8	(Note 9)	_	+395	°C/W
θ _{JC}	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	_	+236	°C/W

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Switching Characteristics

C_L = 5pF, See Figure 1

Parameter	Parameter From		V	T _A = +25°C			$T_A = -40^{\circ}C$	C to +85°C	T _A = -40°C	Unit	
arameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Oiiit
			V8.0	_	19.6	_	_	_	_	_	
		1.2V ± 0.1V	2.5	5.1	11.9	2.1	13.3	2.1	14.7		
	A or D	V	1.5V ± 0.1V	1.6	3.7	6.7	1.4	7.8	1.4	8.6] [
t _{pd} A or B	Y	1.8V ± 0.15V	1.3	3.0	5.3	1.1	6.2	1.1	6.9	ns	
			2.5V ± 0.2V	1.0	2.4	3.9	0.9	4.6	0.9	5.1	
			3.3V ± 0.3V	1.0	2.2	3.4	0.8	4.0	8.0	4.4	

C_L = 10pF, See Figure 1

Parameter	From	То	V		T _A = +25°C	;	$T_A = -40$ °C to +85°C		T _A = -40°C	to +125°C	Unit
Farameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Ullit
			V8.0	_	23.5	_	_	_	_	_	
		1.2V ± 0.1V	2.4	6.0	14.1	2.2	15.7	2.2	17.4]	
	A or B	Y	1.5V ± 0.1V	1.9	4.3	7.9	1.7	9.2	1.7	10.2	ns
lpd	t _{pd} A or B		1.8V ± 0.15V	1.6	3.6	6.2	1.5	7.3	1.5	8.1	
			2.5V ± 0.2V	1.4	3.0	4.7	1.2	5.6	1.2	6.2	
			3.3V ± 0.3V	1.3	2.7	4.2	1.2	5.0	1.2	5.5	

C_L = 15pF, See Figure 1

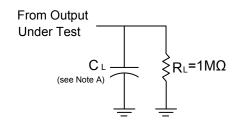
Parameter	From	То	V	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C	to +125°C	Unit
Farameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Oiiit
			V8.0	_	27.5	_	_	_	_	_	
		1.2V ± 0.1V	3.4	6.8	16.1	3.1	20.2	3.1	20.4		
	A or B	_	1.5V ± 0.1V	2.3	4.8	8.9	2.0	10.4	2.0	11.5	ns
t _{pd}	AOIB	T	1.8V ± 0.15V	1.9	4.0	7.0	1.7	8.3	1.7	9.2	
			2.5V ± 0.2V	1.7	3.4	5.4	1.5	6.3	1.5	7.0	
			3.3V ± 0.3V	1.4	3.2	4.8	1.3	5.7	1.3	6.3	

C_L = 30pF, See Figure 1

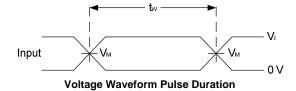
Parameter	From	То	V		T _A = +25°C	;	$T_A = -40^{\circ}C$	to +85°C	T _A = -40°C	to +125°C	Unit
rarameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Ollit
			0.8V	_	39.3	_	_	_	_	_	
		1.2V ± 0.1V	4.6	9.0	21.9	4.1	27.6	4.1	27.8	1	
	A or B	_	1.5V ± 0.1V	3.4	6.4	11.8	2.9	13.9	2.9	15.3] [
τ _{pd}	AUID	I	1.8V ± 0.15V	2.6	5.3	9.3	2.3	11.1	2.3	12.3	ns
			2.5V ± 0.2V	2.4	4.5	7.1	2.1	8.5	2.1	9.4	1
			3.3V ± 0.3V	2.0	4.2	6.4	1.8	7.7	1.8	8.5	

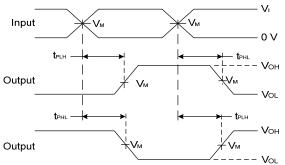


Parameter Measurement Information



V	Inputs		.,	•
Vcc	VI	V_{I} t_{r}/t_{f} V_{M}	VM	CL
0.8V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.2V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.5V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.8V ± 0.15V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
2.5V ± 0.2V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
3.3V ± 0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF





Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
 C. Inputs are measured separately one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$



Marking Information

X2-DFN1210-8

(Top View)

 $\underline{XX}\,:\,$ Identification Code

<u>Y</u> : Year : 0~9

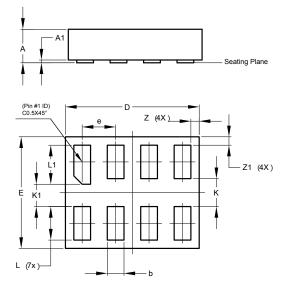
<u>W</u>: week : A~Z : 1~26 week

a~z: 27-52 week

Part Number	Package	Identification Code
74AUP2G02RA3-7	X2-DFN1210-8	ВТ

X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



		-	x	1	-	
A	<u> </u>					
Y1	G —					
	_		; -		_ x _	_

X2-DFN1210-8			
Dim	Min	Max	Тур
Α	-	0.35	0.30
A 1	0	0.03	0.02
b	0.10	0.20	0.15
D	1.15	1.25	1.20
E	0.95	1.05	1.00
е	-	-	0.30
K	-	-	0.25
K1	-	-	0.20
L	0.25	0.35	0.30
L1	0.30	0.40	0.35
Z	0.050	0.100	0.075
Z 1	0.050	0.100	0.075
All Dimensions in mm			

Dimensions	Value (in mm)
С	0.300
G	0.150
X	0.150
X1	1.050
Y	0.500
Y1	1.150



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